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Reference

Design

TPS255xx Precision Adjustable Current-Limited Power-Distribution Switches

Technical

Documents

1 Features

- Up to 1.5-A Maximum Load Current
- ±6% Current-Limit Accuracy at 1.7 A (Typical)
- Meets USB Current-Limiting Requirements
- Backwards Compatible With TPS2550 and TPS2551
- Adjustable Current Limit: 75 mA to 1700 mA (Typical)
- Constant-Current (TPS255x) and Latch-Off (TPS255x-1) Versions
- Fast Overcurrent Response 2 µs (Typical)
- 85-mΩ High-Side MOSFET (DBV Package)
- Reverse Input-Output Voltage Protection
- Operating Range: 2.5 V to 6.5 V
- Built-In Soft Start
- 15-kV ESD Protection per IEC 61000-4-2 (With External Capacitance)
- UL Listed File No. E169910 and NEMKO IEC60950-1-am1 ed2.0
- See the TI Switch Portfolio

2 Applications

- USB Ports and Hubs
- Digital TVs
- Set-Top Boxes
- VOIP Phones

3 Description

Tools &

Software

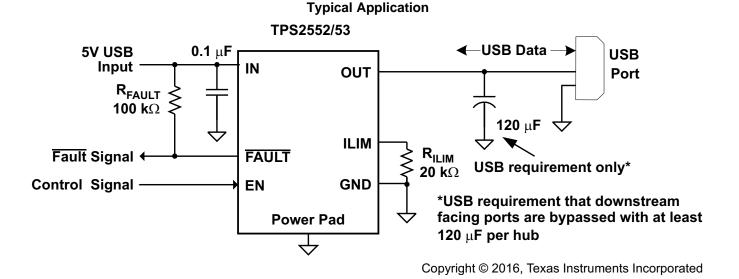
The TPS255x and TPS255x-1 power-distribution switches are intended for applications where precision current limiting is required or heavy capacitive loads and short circuits are encountered and provide up to 1.5 A of continuous load current. These devices offer a programmable current-limit threshold between 75 mA and 1.7 A (typical) through an external resistor. Current-limit accuracy as tight as $\pm 6\%$ can be achieved at the higher current-limit settings. The power-switch rise and fall times are controlled to minimize current surges during turnon and turnoff.

TPS255x devices limit the output current to a safe level by using a constant-current mode when the output load exceeds the current-limit threshold. TPS255x-1 devices provide circuit breaker functionality by latching off the power switch during overcurrent or reverse-voltage situations. An internal reverse-voltage comparator disables the powerswitch when the output voltage is driven higher than the input to protect devices on the input side of the switch. The FAULT output asserts low during overcurrent and reverse-voltage conditions.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)				
TPS2552	SOT-23 (6)	2.90 mm x 1.60 mm				
	WSON (6)	2.00 mm x 2.00 mm				
TPS2553	SOT-23 (6)	2.90 mm x 1.60 mm				
1952553	WSON (6)	2.00 mm x 2.00 mm				

(1) For all available packages, see the orderable addendum at the end of the data sheet.



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4 Revision History

8 9

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision E (February 2012) to Revision F

•	Added ESD Rating table, Feature Description section, Device Functional Modes, Application and Implementation
	section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and
	Mechanical, Packaging, and Orderable Information section
•	Changed 1300 mA to 1700 mA in the adjustable current limit bullet under the Features section

Changed from 1.2 A to 1.5 A.....

Changes from Revision D (June 2011) to Revision E

•	Changed V _{EN} to V _{EN} in Recommended Operating Conditions	6
•	Changed V _{EN} to V _{EN} in Recommended Operating Conditions	. <mark>6</mark>

Changes from Revision C (September 2009) to Revision D

•	Added text to the REVERSE-VOLTAGE PROTECTION section: "A reversewhen this occurs."
	Added ESD-system level (contact/air) to the ABS MAX table, and Added Note 3
•	Changed the DEVICE INFORMATION table, and Deleted Note 3 1
•	Added Features Item "See the TI Switch Portfoilo" 1
•	Added text To Feature - UL Listed "and NEMKO IEC60950-1-am1 ed2.0" 1
•	Changed From: Fast Overcurrent Response - 2-µS (typ) To: Fast Overcurrent Response - 2-µs (typ) in the Features 1

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Changes from Revision B (February 2009) to Revision C

•	Added Feature - Up to 1.5 A Maximum Load Current	. 1
•	Changed 1.3 A (typ) To: 1.7 A (typ)	. 1
•	Added Text - and provide up to 1.5 A of continuous load current	. 1
	Changed From: 19.1 k $\Omega \le R_{ILIM} \le 232 \text{ k}\Omega$ To: 15 k $\Omega \le R_{ILIM} \le 232 \text{ k}\Omega$.	
•	Changed I _{OUT} values for 1.2A and 1.5A	. 6
•	Changed T _J values for 1.2A and 1.5A	. 6
•	Added $R_{ILIM} = 15 \text{ k}\Omega$ option	. 7
•	Changed Text From: current-limit threshold between 75 mA and 1.3 A (typ) To: current-limit threshold between 75 mA and 1.7 A (typ)	13
•	Changed Text From: The recommended 1% resistor range for R_{ILIM} is 19.1 k $\Omega \le R_{ILIM} \le 232 \text{ k}\Omega$ to ensure stability To: The recommended 1% resistor range for R_{ILIM} is 15 k $\Omega \le R_{ILIM} \le 232 \text{ k}\Omega$ to ensure stability	15
•	Changed From: where 19.1 k $\Omega \le R_{ILIM} \le 232 \text{ k}\Omega$. To: where 15 k $\Omega \le R_{ILIM} \le 232 \text{ k}\Omega$.	15
•	Changed Figure 23 - Current-Limit Threshold vs R _{ILIM}	16
•	Changed Table 2 - added rows for Current Limit of 1400 to 1700	19

Changes from Revision A (December 2008) to Revision B

•	Added To Features - UL Listed – File No. E169910	1
•	Changed Figure 17 Ttitle From: Current Limit Threshold Vs R _{ILM}	9
•	Changed Figure 18 Ttitle From: Current Limit Threshold Vs R _{ILM}	9

Changes from Original (November 2008) to Revision A

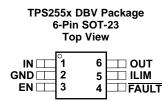
Changed Title from: Adjustable Current Limited Dower Distribution Switches to: Dresision Adjustable Current
Changed Title from: Adjustable Current-Limited Power-Distribution Switches to: Precision Adjustable Current-
Limited Power-Distribution Switches

5 Device Comparison Table

	GENERAL SWITCH CATALOG									
33 mΩ single +0.000 TPS201xA 0.2A-2A TPS202x 0.2A-2A TPS203x 0.2A-2A	80 mΩ, single TPS2014 600 mA TPS2015 1A TPS2041B 500 mA TPS2045A 250 mA TPS2045A 250 mA TPS2045A 250 mA TPS2045A 250 mA TPS2065 1A TPS2065 1A TPS2065 1.5 A	80 mΩ, dual TPS2042B 500 mA TPS2042B 500 mA TPS2046B 250 mA TPS2046B 250 mA TPS2062 1 A TPS2062 1 A TPS2062 1.5 A TPS2064 1.5 A	80 mΩ, dual TPS2080 500 mA TPS2081 500 mA TPS2082 500 mA TPS2090 250 mA TPS2092 250 mA	80 mΩ, triple 1 PS2043B 500 mA TPS2043B 500 mA TPS2047B 250 mA TPS2047B 250 mA TPS2057A 250 mA TPS2063 1 A TPS2067 1 A		80 mΩ, quad + 0 0 + + + + + + + + + + + + + + + + +				



6 Pin Configuration and Functions



EN = Active Low for the TPS2552

EN = Active High for the TPS2553

Add -1 to part number for latch-off version



EN = Active Low for the TPS2552 EN = Active High for the TPS2553 Add –1 to part number for latch-off version

PIN								
	TPS2552		TPS2553		I/O	DESCRIPTION		
NAME	SOT-23	WSON	SOT-23	WSON	-			
EN	3	4	—	_	I	Enable input, logic low turns on power switch		
EN	—	—	3	4	I	Enable input, logic high turns on power switch		
FAULT	4	3	4	3	0	Active-low open-drain output, asserted during overcurrent, overtemperature, or reverse-voltage conditions.		
GND	2	5	2	5	_	Ground connection; connect externally to PowerPAD		
ILIM	5	2	5	2	0	External resistor used to set current-limit threshold; recommended 15 k $\Omega \le R_{ILIM} \le 232 \text{ k}\Omega$.		
IN	1	6	1	6	I	Input voltage; connect a 0.1 μ F or greater ceramic capacitor from IN to GND as close to the IC as possible.		
OUT	6	1	6	1	0	Power-switch output		
PowerPAD™		PAD	_	PAD	_	Internally connected to GND; used to heat-sink the part to the circuit board traces. Connect PowerPAD to GND pin externally.		

Pin Functions

Add –1 for Latch-Off version

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)(2)

		MIN	MAX	UNIT
	Voltage range on IN, OUT, EN or EN, ILIM, FAULT	-0.3	7	V
	Voltage range from IN to OUT	-7	7	V
Ιo	Continuous output current	Internally	/ Limited	
	Continuous total power dissipation	See the Thern	nal Information	
	Continuous FAULT sink current	0	25	mA
	ILIM source current	0	1	mA
T_J	Maximum junction temperature	-40	150	°C
T _{stg}	Storage temperature	-65	150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) Voltages are referenced to GND unless otherwise noted.

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TRUMENTS

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7.2 ESD Ratings

			VALUE	UNIT	
		Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000		
V _(ESD)	V(ESD) Electrostatic discharge	Charged device model (CDM), per JEDEC specification JESD22-C101 $^{(2)}$	±500	V	
()		IEC 61000-4-2 contact discharge ⁽³⁾	±8000		
		IEC 61000-4-2 air-gap discharge ⁽³⁾	±15000		

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

(3) Surges per EN61000-4-2. 1999 applied to output terminals of EVM. These are passing test levels, not failure threshold.

7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	NOM MAX	UNIT
V _{IN}	Input voltage, IN		2.5	6.5	V
VEN	Enable voltage	TPS2552/52-1	0	6.5	V
V_{EN}	Enable voltage	TPS2553/53-1	0	6.5	V
VIH	High-level input voltage on EN	l or EN	1.1		V
VIL	Low-level input voltage on EN	or EN		0.66	V
	Continuous output current,	–40 °C ≤ T _J ≤ 125 °C	0	1.2	٨
IOUT	OUT	–40 °C ≤ T _J ≤ 105 °C	0	1.5	A
R _{ILIM}	Current-limit threshold resistor	range (nominal 1%) from ILIM to GND	15	232	kΩ
I _O	Continuous FAULT sink curre	nt	0	10	mA
	Input de-coupling capacitance	, IN to GND	0.1		μF
-	Operating virtual junction	I _{OUT} ≤ 1.2 A	-40	125	°C
IJ	Operating virtual junction temperature ⁽¹⁾	I _{OUT} ≤ 1.5 A	-40	105	۰C

(1) See Power Dissipation and Junction Temperature for details on how to calculate maximum junction temperature for specific applications and packages.

7.4 Thermal Information

		TPS2	552	TPS	2553	
	THERMAL METRIC ⁽¹⁾	DBV (SOT-23)	DRV (WSON)	DBV (SOT-23)	DRV (WSON)	UNIT
		6 PINS	6 PINS	6 PINS	6 PINS	
R_{\thetaJA}	Junction-to-ambient thermal resistance	182.6	72	182.6	72	°C/W
R _{θJC(to} p)	Junction-to-case (top) thermal resistance	122.2	85.3	122.2	85.3	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	29.4	41.3	29.4	41.3	°C/W
ΨJT	Junction-to-top characterization parameter	20.8	1.7	20.8	1.7	°C/W
ΨЈВ	Junction-to-board characterization parameter	28.9	41.7	28.9	41.7	°C/W
R _{0JC(b}	Junction-to-case (bottom) thermal resistance	_	11.1	_	11.1	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

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7.5 Electrical Characteristics

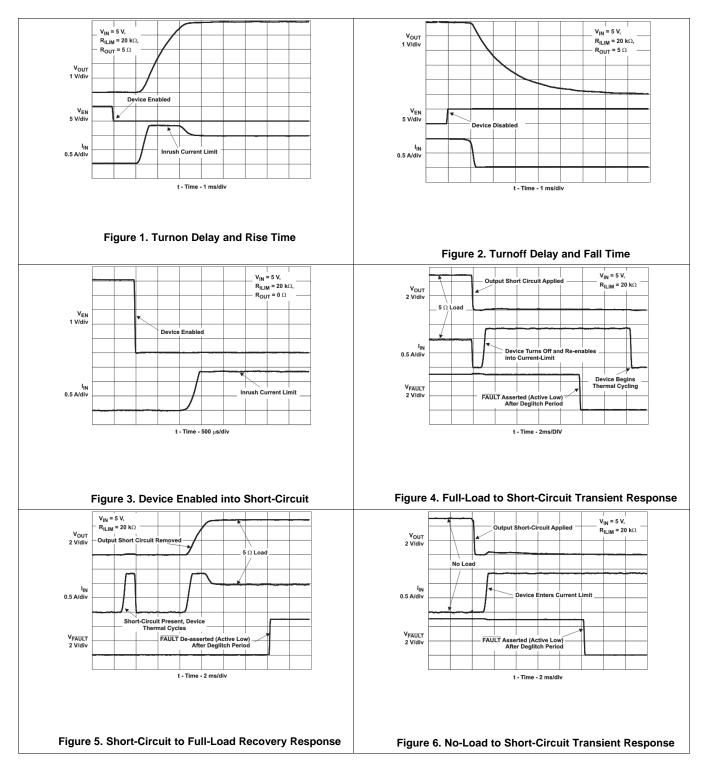
over recommended operating conditions, $V_{EN} = 0$ V, or $V_{EN} = V_{IN}$, $R_{FAULT} = 10$ k Ω (unless otherwise noted)

	PARAMETER	TEST CON	DITIONS ⁽¹⁾	MIN	TYP	MAX	UNIT
POWE	R SWITCH						
		DBV package, T _J = 25°C			85	95	
		DBV package, –40°C ≤T _J ≤125°C				135	
DS(on)	Static drain-source on-state resistance	DRV package, T _J = 25°C		100	115	mΩ	
		DRV package, –40°C ≤T _J ≤105°C			140		
		DRV package, –40°C ≤T _J ≤125°C			150		
		$C_{L} = 1 \ \mu F, R_{L} = 100 \ \Omega,$	V _{IN} = 6.5 V		1.1	1.5	
r	Rise time, output	(see Figure 20)	V _{IN} = 2.5 V		0.7	1	
		$C_{L} = 1 \ \mu F, R_{L} = 100 \ \Omega,$	V _{IN} = 6.5 V	0.2		0.5	ms
t _f	Fall time, output	(see Figure 20)	V _{IN} = 2.5 V	0.2		0.5	
ENABI							
	Enable pin turn on/off threshold			0.66		1.1	V
EN	Input current	V _{EN} = 0 V or 6.5 V, V _{EN} = 0 V or 6.5 V	1	-0.5		0.5	μA
t _{on}	Turnon time	$C_{L} = 1 \ \mu F, R_{L} = 100 \ \Omega$, (see Figure 20				3	ms
t _{off}	Turnoff time	$C_L = 1 \ \mu\text{F}, R_L = 100 \ \Omega$, (see Figure 20			3	ms	
	ENT LIMIT			I		-	
		R _{ILIM} = 15 kΩ, −40°C ≤T _J ≤105°C		1610	1700	1800	
		······ · · · · · · · · · · · · · · · ·	T _{.1} = 25°C	1215	1295	1375	
	Current-limit threshold (Maximum DC	$R_{ILIM} = 20 \ k\Omega$	–40°C ≤T, ≤125°C	1200	1295	1375	
OS	output current IOUT delivered to load)		$T_1 = 25^{\circ}C$	490	520	550	mA
05	and Short-circuit current, OUT connected to GND	$R_{ILIM} = 49.9 \text{ k}\Omega$	-40°C ≤T, ≤125°C	475	520	565	110 (
		R _{IIIM} = 210 kΩ	-40 0 31 3120 0	110	130	150	
		ILIM shorted to IN		50	75	100	
	Posponso timo to short circuit	$V_{IN} = 5 V$ (see Figure 21)	50	2	100	110	
	Response time to short circuit	VIN = 3 V (see Figure 21)			2		μs
	Reverse-voltage comparator trip point (V _{OUT} - V _{IN})			95	135	190	mV
	Time from reverse-voltage condition to MOSFET turn off	V _{IN} = 5 V		3	5	7	ms
SUPPL	Y CURRENT	· · · · · · · · · · · · · · · · · · ·					
IN_off	Supply current, low-level output	$V_{IN} = 6.5 \text{ V}$, No load on OUT, $V_{\overline{EN}} = 6$			0.1	1	μA
IN_on	Supply current, high-level output	$V_{IN} = 6.5 V$, No load on OUT	$R_{ILIM} = 20 \ k\Omega$		120	140	μA
			R _{ILIM} = 210 kΩ		100	120	μA
REV	Reverse leakage current	$V_{OUT} = 6.5 \text{ V}, V_{IN} = 0 \text{ V}$	T _J = 25 °C		0.01	1	μA
	RVOLTAGE LOCKOUT						
UVLO	Low-level input voltage, IN	V _{IN} rising			2.35	2.45	V
	Hysteresis, IN	T _J = 25 °C			25		mV
-	FLAG						
V _{OL}	Output low voltage, FAULT	I _{/FAULT} = 1 mA				180	mV
	Off-state leakage	V _{/FAULT} = 6.5 V				1	μA
	FAULT deglitch	FAULT assertion or de-assertion due	to overcurrent condition	5	7.5	10	ms
		FAULT assertion or de-assertion due	to reverse-voltage condition	2	4	6	ms
THER	AL SHUTDOWN						
	Thermal shutdown threshold			155			°C
	Thermal shutdown threshold in current-limit			135			°C

(1) Pulse-testing techniques maintain junction temperature close to ambient temperature; thermal effects must be taken into account separately.



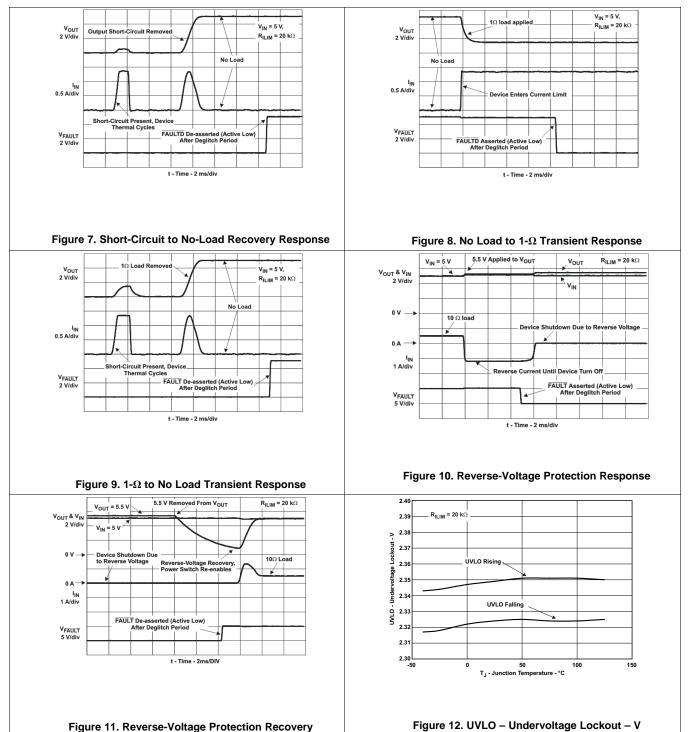
7.6 Typical Characteristics



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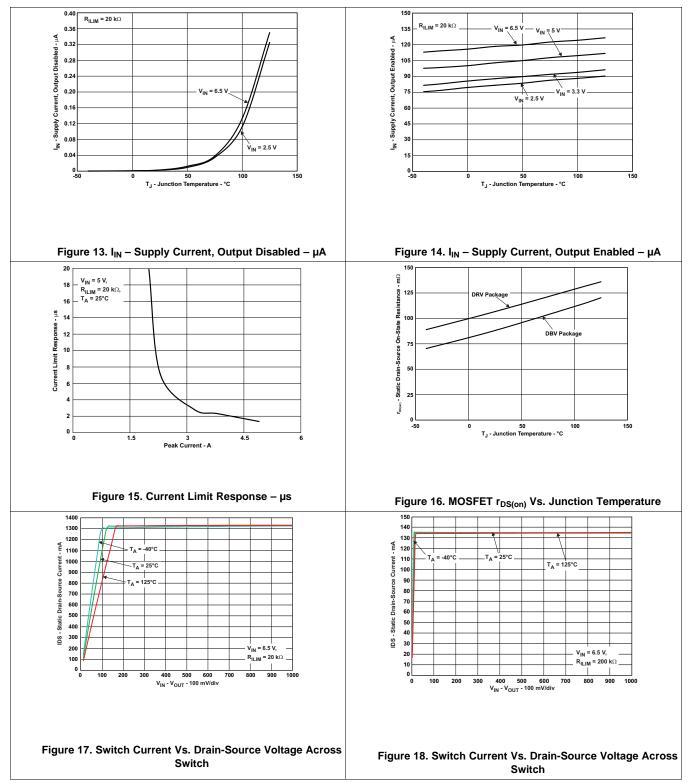


Typical Characteristics (continued)





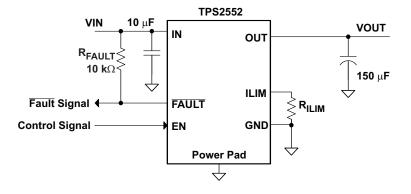
Typical Characteristics (continued)



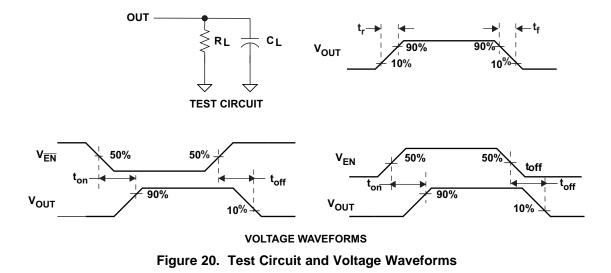
Product Folder Links: TPS2552 TPS2553 TPS2552-1 TPS2553-1



8 Parameter Measurement Information







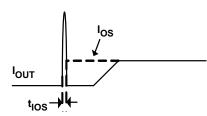


Figure 21. Response Time to Short-Circuit Waveform

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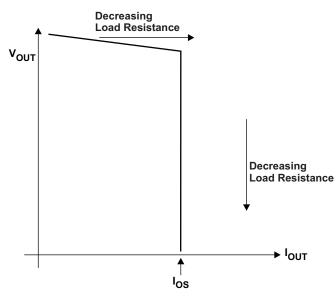


Figure 22. Output Voltage vs Current-Limit Threshold

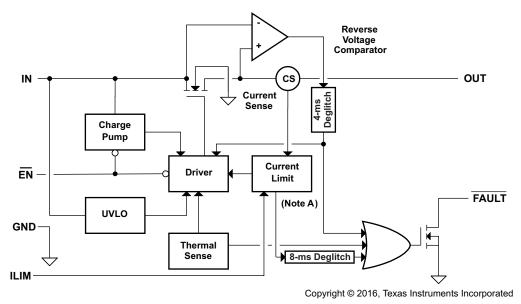


9 Detailed Description

9.1 Overview

The TPS255x and TPS255x-1 are current-limited, power-distribution switches using N-channel MOSFETs for applications where short circuits or heavy capacitive loads are encountered and provide up to 1.5 A of continuous load current. These devices allow the user to program the current-limit threshold between 75 mA and 1.7 A (typical) through an external resistor. Additional device shutdown features include overtemperature protection and reverse-voltage protection. The device incorporates an internal charge pump and gate drive circuitry necessary to drive the N-channel MOSFET. The charge pump supplies power to the driver circuit and provides the necessary voltage to pull the gate of the MOSFET above the source. The charge pump operates from input voltages as low as 2.5 V and requires little supply current. The driver controls the gate voltage of the power switch. The driver incorporates circuitry that controls the rise and fall times of the output voltage to limit large current and voltage surges and provides built-in soft-start functionality. There are two device families that handle overcurrent situations differently. The TPS255x family enters constant-current mode while the TPS255x-1 family latches off when the load exceeds the current-limit threshold.

9.2 Functional Block Diagram



A. TPS255x parts enter constant current mode during current limit condition; TPS255x-1 parts latch off

9.3 Feature Description

9.3.1 Overcurrent Conditions

The TPS255x and TPS255x-1 respond to overcurrent conditions by limiting their output current to the I_{OS} levels shown in Figure 23. When an overcurrent condition is detected, the device maintains a constant output current and reduces the output voltage accordingly. Two possible overload conditions can occur.

The first condition is when a short circuit or partial short circuit is present when the device is powered-up or enabled. The output voltage is held near zero potential with respect to ground and the TPS255x ramps the output current to I_{OS} . The TPS255x devices limits the current to I_{OS} until the overload condition is removed or the device begins to thermal cycle. The TPS255x-1 devices will limit the current to I_{OS} until the overload condition is removed or the internal deglitch time (7.5-ms typical) is reached and the device is turned off. The device remains off until power is cycled or the device enable is toggled.

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Feature Description (continued)

The second condition is when a short circuit, partial short circuit, or transient overload occurs while the device is enabled and powered on. The device responds to the overcurrent condition within time t_{IOS} (see Figure 21). The current-sense amplifier is overdriven during this time and momentarily disables the internal current-limit MOSFET. The current-sense amplifier recovers and limits the output current to I_{OS} . Similar to the previous case, the TPS255x limits the current to I_{OS} until the overload condition is removed or the device begins to thermal cycle; the TPS255x-1 limits the current to I_{OS} until the overload condition is removed or the internal deglitch time is reached and the device is latched off.

The TPS255x thermal cycles if an overload condition is present long enough to activate thermal limiting in any of the above cases. The device turns off when the junction temperature exceeds 135°C (typical) while in current limit. The device remains off until the junction temperature cools 10°C (typical) and then restarts. The TPS255x cycles on and off until the overload is removed (see Figure 5 and Figure 7).

9.3.2 Reverse-Voltage Protection

The reverse-voltage protection feature turns off the N-channel MOSFET whenever the output voltage exceeds the input voltage by 135 mV (typical) for 4-ms (typical). A reverse current of $(V_{OUT} - V_{IN})/r_{DS(on)}$) are present when this occurs. This prevents damage to devices on the input side of the TPS255x and TPS2552-1/TPS2253-1 by preventing significant current from sinking into the input capacitance. The TPS255x devices allow the N-channel MOSFET to turn on once the output voltage goes below the input voltage for the same 4-ms deglitch time. The TPS255x-1 devices keep the device turned off even if the reverse-voltage condition is removed and do not allow the N-channel MOSFET to turn on until power is cycled or the device enable is toggled. The reverse-voltage comparator also asserts the FAULT output (active-low) after 4-ms.

9.3.3 FAULT Response

The FAULT open-drain output is asserted (active low) during an overcurrent, overtemperature, or reverse-voltage condition. The TPS255x asserts the FAULT signal until the fault condition is removed and the device resumes normal operation. The TPS255x-1 asserts the FAULT signal during a fault condition and remains asserted while the part is latched-off. The FAULT signal is de-asserted once device power is cycled or the enable is toggled and the device resumes normal operation. The TPS255x and TPS255x-1 are designed to eliminate false FAULT reporting by using an internal delay *de-glitch* circuit for overcurrent (7.5-ms typical) and reverse-voltage (4-ms typical) conditions without the need for external circuitry. This ensures that FAULT is not accidentally asserted due to normal operation such as starting into a heavy capacitive load. The deglitch circuitry delays entering and leaving fault conditions. Overtemperature conditions are not deglitched and assert the FAULT signal immediately.

9.3.4 Undervoltage Lockout (UVLO)

The undervoltage lockout (UVLO) circuit disables the power switch until the input voltage reaches the UVLO turnon threshold. Built-in hysteresis prevents unwanted on and off cycling due to input voltage drop from large current surges.

9.3.5 ENABLE (EN or EN)

The logic enable controls the power switch, bias for the charge pump, driver, and other circuits to reduce the supply current. The supply current is reduced to less than $1-\mu A$ when a logic low is present on EN. A logic low input on EN or a logic high input on EN enables the driver, control circuits, and power switch. The enable input is compatible with both TTL and CMOS logic levels.

9.3.6 Thermal Sense

The TPS255x and TPS255x-1 have self-protection features using two independent thermal-sensing circuits that monitor the operating temperature of the power switch and disable operation if the temperature exceeds recommended operating conditions. The TPS255x device operates in constant-current mode during an overcurrent conditions, which increases the voltage drop across power-switch. The power dissipation in the package is proportional to the voltage drop across the power switch, which increases the junction temperature during an overcurrent condition. The first thermal sensor turns off the power switch when the die temperature exceeds 135°C (minimum) and the part is in current limit. Hysteresis is built into the thermal sensor, and the switch turns on after the device has cooled approximately 10°C.

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Product Folder Links: TPS2552 TPS2553 TPS2552-1 TPS2553-1



Feature Description (continued)

The TPS255x and TPS255x-1 also have a second ambient thermal sensor. The ambient thermal sensor turns off the power-switch when the die temperature exceeds 155°C (minimum) regardless of whether the power switch is in current limit and turns on the power switch after the device has cooled approximately 10°C. The TPS255x and TPS255x-1 families continue to cycle off and on until the fault is removed.

The open-drain fault reporting output FAULT is asserted (active low) immediately during an overtemperature shutdown condition.

9.4 Device Functional Modes

There are no other functional modes.

9.5 Programming

9.5.1 Programming the Current-Limit Threshold

The overcurrent threshold is user programmable through an external resistor. The TPS255x and TPS255x-1 use an internal regulation loop to provide a regulated voltage on the ILIM pin. The current-limit threshold is proportional to the current sourced out of ILIM. The recommended 1% resistor range for R_{ILIM} is 15 k $\Omega \le R_{ILIM} \le$ 232 k Ω to ensure stability of the internal regulation loop. Many applications require that the minimum current limit is above a certain current level or that the maximum current limit is below a certain current level, so it is important to consider the tolerance of the overcurrent threshold when selecting a value for R_{ILIM}. The following equations and Figure 23 can be used to calculate the resulting overcurrent threshold for a given external resistor value (R_{ILIM}). Figure 23 includes current-limit tolerance due to variations caused by temperature and process. However, the equations do not account for tolerance due to external resistor variation, so it is important to account for this tolerance when selecting R_{ILIM}. The traces routing the R_{ILIM} resistor to the TPS255x and TPS255x-1 must be as short as possible to reduce parasitic effects on the current-limit accuracy.

R_{ILIM} can be selected to provide a current-limit threshold that occurs 1) above a minimum load current or 2) below a maximum load current.

To design above a minimum current-limit threshold, find the intersection of R_{ILIM} and the maximum desired load current on the $I_{OS(min)}$ curve and choose a value of R_{ILIM} below this value. Programming the current limit above a minimum threshold is important to ensure start-up into full load or heavy capacitive loads. The resulting maximum current-limit threshold is the intersection of the selected value of R_{ILIM} and the $I_{OS(max)}$ curve.

To design below a maximum current-limit threshold, find the intersection of R_{ILIM} and the maximum desired load current on the $I_{OS(max)}$ curve and choose a value of R_{ILIM} above this value. Programming the current limit below a maximum threshold is important to avoid current limiting upstream power supplies, causing the input voltage bus to droop. The resulting minimum current-limit threshold is the intersection of the selected value of R_{ILIM} and the $I_{OS(min)}$ curve.

Current-Limit Threshold Equations (I_{OS}):

$$I_{OSmax}(mA) = \frac{22980V}{R_{ILIM}^{0.94}k\Omega}$$
$$I_{OSnom}(mA) = \frac{23950V}{R_{ILIM}^{0.977}k\Omega}$$
$$I_{OSmin}(mA) = \frac{25230V}{R_{ILIM}^{1.016}k\Omega}$$

where

 $15 \text{ k}\Omega \leq \text{R}_{\text{ILIM}} \leq 232 \text{ k}\Omega.$

(1)

While the maximum recommended value of RILIM is 232 k Ω , there is one additional configuration that allows for a lower current-limit threshold. The ILIM pin may be connected directly to IN to provide a 75 mA (typical) current-limit threshold. Additional low-ESR ceramic capacitance may be necessary from IN to GND in this configuration to prevent unwanted noise from coupling into the sensitive ILIM circuitry.

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Programming (continued)

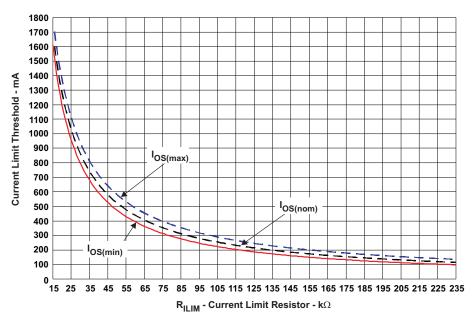


Figure 23. Current-Limit Threshold vs R_{ILIM}



10 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

10.1 Application Information

10.1.1 Constant-Current vs Latch-Off Operation and Impact on Output Voltage

Both the constant-current devices (TPS255x) and latch-off devices (TPS255x-1) operate identically during normal operation, that is, the load current is less than the current-limit threshold and the devices are not limiting current. During normal operation the N-channel MOSFET is fully enhanced, and $V_{OUT} = V_{IN} - (I_{OUT} \times r_{DS(on)})$. The voltage drop across the MOSFET is relatively small compared to V_{IN} , and $V_{OUT} \neq V_{IN}$.

Both the constant-current devices (TPS255x) and latch-off devices (TPS255x-1) operate identically during the initial onset of an overcurrent event. Both devices limit current to the programmed current-limit threshold set to R_{ILIM} by operating the N-channel MOSFET in the linear mode. During current-limit operation, the N-channel MOSFET is no longer fully-enhanced and the resistance of the device increases. This allows the device to effectively regulate the current to the current-limit threshold. The effect of increasing the resistance of the MOSFET is that the voltage drop across the device is no longer negligible ($V_{IN} \neq V_{OUT}$), and V_{OUT} decreases. The amount that V_{OUT} decreases is proportional to the magnitude of the overload condition. The expected V_{OUT} can be calculated by,

 $I_{OS} \times R_{LOAD}$

where

 I_{OS} is the current-limit threshold and R_{LOAD} is the magnitude of the overload condition. (2)

For example, if I_{OS} is programmed to 1 A and a 1 Ω overload condition is applied, the resulting V_{OUT} is 1 V.

While both the constant-current devices (TPS255x) and latch-off devices (TPS255x-1) operate identically during the initial onset of an overcurrent event, they behave differently if the overcurrent event lasts longer than the internal delay *de-glitch* circuit (7.5-ms typical). The constant-current devices (TPS255x) assert the FAULT flag after the deglitch period and continue to regulate the current to the current-limit threshold indefinitely. In practical circuits, the power dissipation in the package increases the die temperature above the overtemperature shutdown threshold (135°C minimum), and the device turns off until the die temperature decreases by the hysteresis of the thermal shutdown circuit (10°C typical). The devices resume normal operation once the overload condition is removed. The constant-current devices resume normal operation once the overload immediately turn off the device. The device remains off regardless of whether the overload condition is removed from the output. The latch-off devices remain off and do not resume normal operation until the surrounding system either toggles the enable or cycles power to the device.

10.2 Typical Applications

10.2.1 Two-Level Current-Limit Circuit

Some applications require different current-limit thresholds depending on external system conditions. Figure 24 shows an implementation for an externally controlled, two-level current-limit circuit. The current-limit threshold is set by the total resistance from ILIM to GND (see the *Programming the Current-Limit Threshold* section). A logic-level input enables or disables MOSFET Q1 and changes the current-limit threshold by modifying the total resistance from ILIM to GND. Additional MOSFET and resistor combinations can be used in parallel to Q1/R2 to increase the number of additional current-limit levels.

NOTE ILIM must never be driven directly with an external signal.

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Typical Applications (continued)

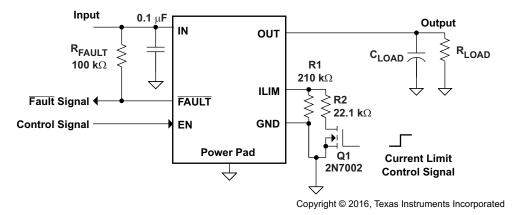


Figure 24. Two-Level Current-Limit Circuit

10.2.1.1 Design Requirements

For this example, use the parameters shown in Table 1.

Table 1. Design Requirements

PARAMETER	VALUE
Input voltage	5 V
Output voltage	5 V
Above a minimum current limit	1000 mA
Below a maximum current limit	500 mA

10.2.1.2 Detailed Design Procedures

10.2.1.2.1 Designing Above a Minimum Current Limit

Some applications require that current limiting cannot occur below a certain threshold. For this example, assume that 1 A must be delivered to the load so that the minimum desired current-limit threshold is 1000 mA. Use the I_{OS} equations and Figure 23 to select R_{ILIM}.

$$I_{OSmin}(mA) = 1000mA$$

$$I_{OSmin}(mA) = \frac{25230V}{R_{ILIM}^{1.016}k\Omega}$$

$$R_{ILIM}(k\Omega) = \left(\frac{25230V}{I_{OSmin}mA}\right)^{\frac{1}{1.016}}$$

$$R_{ILIM}(k\Omega) = 24k\Omega$$

(3)

Select the closest 1% resistor less than the calculated value: $R_{ILIM} = 23.7 \text{ k}\Omega$. This sets the minimum current-limit threshold at 1 A. Use the I_{OS} equations, Figure 23, and the previously calculated value for R_{ILIM} to calculate the maximum resulting current-limit threshold.

$$R_{ILIM}(k\Omega) = 23.7k\Omega$$

$$I_{OSmax}(mA) = \frac{22980V}{R_{ILIM}^{0.94}k\Omega}$$

$$I_{OSmax}(mA) = \frac{22980V}{23.7^{0.94}k\Omega}$$

$$I_{OSmax}(mA) = 1172.4mA$$

The resulting maximum current-limit threshold is 1172.4 mA with a 23.7-k Ω resistor.



10.2.1.2.2 Designing Below a Maximum Current Limit

Some applications require that current limiting must occur below a certain threshold. For this example, assume that the desired upper current-limit threshold must be below 500 mA to protect an up-stream power supply. Use the I_{OS} equations and Figure 23 to select R_{ILIM} .

$$I_{OSmax}(mA) = 500mA$$

$$I_{OSmax}(mA) = \frac{22980V}{R_{ILIM}^{0.94}k\Omega}$$

$$R_{ILIM}(k\Omega) = \left(\frac{22980V}{I_{OSmax}mA}\right)^{\frac{1}{0.94}}$$

$$R_{ILIM}(k\Omega) = 58.7k\Omega$$

(5)

Select the closest 1% resistor greater than the calculated value: $R_{ILIM} = 59$ -k Ω . This sets the maximum current-limit threshold at 500 mA . Use the I_{OS} equations, Figure 23, and the previously calculated value for R_{ILIM} to calculate the minimum resulting current-limit threshold.

$$R_{ILIM}(k\Omega) = 59k\Omega$$

$$I_{OSmin}(mA) = \frac{25230V}{R_{ILIM}^{1.016}k\Omega}$$

$$I_{OSmin}(mA) = \frac{25230V}{59^{1.016}k\Omega}$$

$$I_{OSmin}(mA) = 400.6mA$$

(6)

The resulting minimum current-limit threshold is 400.6 mA with a 59-k Ω resistor.

10.2.1.2.3 Accounting for Resistor Tolerance

The previous sections described the selection of R_{ILIM} given certain application requirements and the importance of understanding the current-limit threshold tolerance. The analysis focused only on the TPS255x and TPS255x-1 performance and assumed an exact resistor value. However, resistors sold in quantity are not exact and are bounded by an upper and lower tolerance centered around a nominal resistance. The additional R_{ILIM} resistance tolerance directly affects the current-limit threshold accuracy at a system level. The following table shows a process that accounts for worst-case resistor tolerance assuming 1% resistor values. Step one follows the selection process outlined in the application examples above. Step two determines the upper and lower resistance bounds of the selected resistor. Step three uses the upper and lower resistor bounds in the I_{OS} equations to calculate the threshold limits. It is important to use tighter tolerance resistors, for example, 0.5% or 0.1%, when precision current limiting is desired.

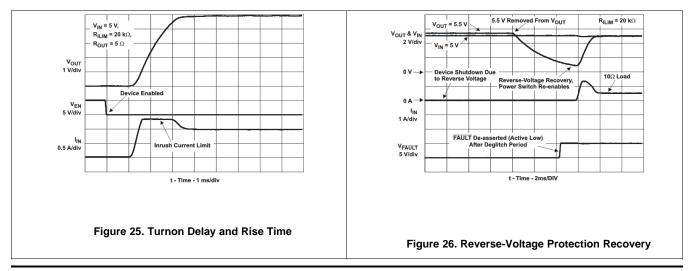
	Table 2. Common R _{ILIM} Resistor Selections												
DESIRED			RESISTOR 1	OLERANCE		ACTUAL LIMITS							
NOMINAL CURRENT LIMIT (mA)	IDEAL RESISTOR (kΩ)	CLOSEST 1% RESISTOR (kΩ)	1% LOW (kΩ)	1% HIGHT (kΩ)	IOS MIN (mA)	IOS NOM (mA)	IOS MAX (mA)						
75		SHORT I	LIM to IN		50.0	75.0	100.0						
120	226.1	226	223.7	228.3	101.3	120.0	142.1						
200	134.0	133	131.7	134.3	173.7	201.5	233.9						
300	88.5	88.7	87.8	89.6	262.1	299.4	342.3						
400	65.9	66.5	65.8	67.2	351.2	396.7	448.7						
500	52.5	52.3	51.8	52.8	448.3	501.6	562.4						
600	43.5	43.2	42.8	43.6	544.3	604.6	673.1						
700	37.2	37.4	37.0	37.8	630.2	696.0	770.8						
800	32.4	32.4	32.1	32.7	729.1	800.8	882.1						
900	28.7	28.7	28.4	29.0	824.7	901.5	988.7						
1000	25.8	26.1	25.8	26.4	908.3	989.1	1081.0						
1100	23.4	23.2	23.0	23.4	1023.7	1109.7	1207.5						
1200	21.4	21.5	21.3	21.7	1106.0	1195.4	1297.1						
1300	19.7	19.6	19.4	19.8	1215.1	1308.5	1414.9						
1400	18.3	18.2	18.0	18.4	1310.1	1406.7	1517.0						
1500	17.0	16.9	16.7	17.1	1412.5	1512.4	1626.4						
1600	16.0	15.8	15.6	16.0	1512.5	1615.2	1732.7						
1700	15.0	15.0	14.9	15.2	1594.5	1699.3	1819.4						

Table 2. Common R_{ILIM} Resistor Selections

10.2.1.2.4 Input and Output Capacitance

Input and output capacitance improves the performance of the device; the actual capacitance must be optimized for the particular application. For all applications, TI recommends placing a $0.1-\mu$ F or greater ceramic bypass capacitor between IN and GND as close to the device as possible for local noise de-coupling. This precaution reduces ringing on the input due to power-supply transients. Additional input capacitance may be needed on the input to reduce voltage overshoot from exceeding the absolute maximum voltage of the device during heavy transient conditions. This is especially important during bench testing when long, inductive cables are used to connect the evaluation board to the bench power-supply.

TI recommends placing a high-value electrolytic capacitor on the output pin when large transient currents are expected on the output.



10.2.1.3 Application Curves

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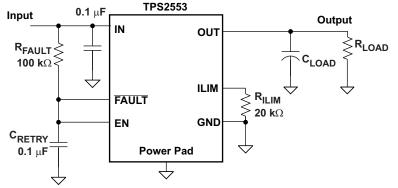
Product Folder Links: TPS2552 TPS2553 TPS2552-1 TPS2553-1

www.ti.com



10.2.2 Auto-Retry Functionality

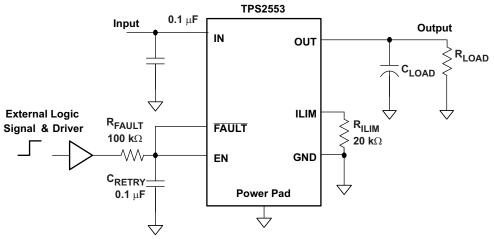
Some applications require that an overcurrent condition disables the part momentarily during a fault condition and re-enables after a pre-set time. This *auto-retry* functionality can be implemented with an external resistor and capacitor. During a fault condition, FAULT pulls low disabling the part. The part is disabled when EN is pulled low, and FAULT goes high impedance allowing C_{RETRY} to begin charging. The part re-enables when the voltage on EN reaches the turnon threshold, and the auto-retry time is determined by the resistor-capacitor time constant. The device continues to cycle in this manner until the fault condition is removed.



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Figure 27. Auto-Retry Functionality

Some applications require auto-retry functionality and the ability to enable or disable with an external logic signal. Figure 28 shows how an external logic signal can drive EN through R_{FAULT} and maintain auto-retry functionality. The resistor-capacitor time constant determines the auto-retry time-out period.



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Figure 28. Auto-Retry Functionality With External EN Signal

10.2.2.1 Design Requirements

For this example, use the parameters shown in Table 3.

Table 3. Design Requirements

PARAMETER	VALUE
Input voltage	5 V
Output voltage	5 V
Current	1200 mA

TPS2552, TPS2553, TPS2552-1, TPS2553-1

SLVS841F-NOVEMBER 2008-REVISED AUGUST 2016

10.2.2.2 Detailed Design Procedure

Refer to Programming the Current-Limit Threshold section for the current limit setting. For auto-retry functionality, once FAULT asserted, EN pull low, TPS2553 is disabled, FAULT des-asserted, C_{RETRY} is slowly charged to EN logic high through R_{FAULT} , then enable, after deglitch time, FAULT asserted again. In the event of an overload, TPS2553 cycles and has output average current. ON-time with output current is decided by FAULT deglitch time. OFF-time without output current is decided by $R_{FAULT} \times C_{RETRY}$ to get the desired output average current during overload.

10.2.3 Typical Application as USB Power Switch

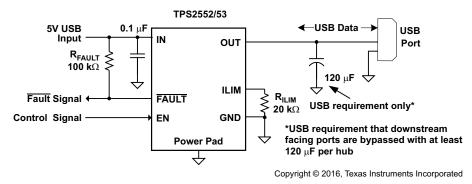


Figure 29. Typical Application as USB Power Switch

10.2.3.1 Design Requirements

For this example, use the parameters shown in Table 4.

Table 4. Design Requirements

PARAMETER	VALUE
Input voltage	5 V
Output voltage	5 V
Current	1200 mA

10.2.3.1.1 USB Power-Distribution Requirements

USB can be implemented in several ways regardless of the type of USB device being developed. Several powerdistribution features must be implemented.

- SPHs must:
 - Current limit downstream ports
 - Report overcurrent conditions
- BPHs must:
 - Enable or disable power to downstream ports
 - Power up at <100 mA
 - Limit inrush current (<44 Ω and 10 μ F)
- Functions must:
 - Limit inrush currents
 - Power up at <100 mA

The feature set of the TPS255x and TPS255x-1 meets each of these requirements. The integrated current limiting and overcurrent reporting is required by self-powered hubs. The logic-level enable and controlled rise times meet the need of both input and output ports on bus-powered hubs and the input ports for bus-powered functions.



TPS2552, TPS2553, TPS2552-1, TPS2553-1 SLVS841F – NOVEMBER 2008 – REVISED AUGUST 2016

10.2.3.2 Detailed Design Procedure

10.2.3.2.1 Universal Serial Bus (USB) Power-Distribution Requirements

One application for this device is for current limiting in universal serial bus (USB) applications. The original USB interface was a 12-Mbps or 1.5-Mbps, multiplexed serial bus designed for low-to-medium bandwidth PC peripherals (for example, keyboards, printers, scanners, and mice). As the demand for more bandwidth increased, the USB 2.0 standard was introduced increasing the maximum data rate to 480-Mbps. The four-wire USB interface is conceived for dynamic attach-detach (hot plug-unplug) of peripherals. Two lines are provided for differential data, and two lines are provided for 5-V power distribution.

USB data is a 3.3-V level signal, but power is distributed at 5 V to allow for voltage drops in cases where power is distributed through more than one hub across long cables. Each function must provide its own regulated 3.3 V from the 5-V input or its own internal power supply. The USB specification classifies two different classes of devices depending on its maximum current draw. A device classified as low-power can draw up to 100 mA as defined by the standard. A device classified as high-power can draw up to 500 mA. It is important that the minimum current-limit threshold of the current-limiting power-switch exceed the maximum current-limit draw of the intended application. The latest USB standard must always be referenced when considering the current-limit threshold

The USB specification defines two types of devices as hubs and functions. A USB hub is a device that contains multiple ports for different USB devices to connect and can be self-powered (SPH) or bus-powered (BPH). A function is a USB device that is able to transmit or receive data or control information over the bus. A USB function can be embedded in a USB hub. A USB function can be one of three types included in the list below.

- Low-power, bus-powered function
- High-power, bus-powered function
- Self-powered function

SPHs and BPHs distribute data and power to downstream functions. The TPS255x has higher current capability than required for a single USB port allowing it to power multiple downstream ports.

11 Power Supply Recommendations

11.1 Self-Powered and Bus-Powered Hubs

A SPH has a local power supply that powers embedded functions and downstream ports. This power supply must provide between 4.75 V to 5.25 V to downstream facing devices under full-load and no-load conditions. SPHs are required to have current-limit protection and must report overcurrent conditions to the USB controller. Typical SPHs are desktop PCs, monitors, printers, and stand-alone hubs.

A BPH obtains all power from an upstream port and often contains an embedded function. It must power up with less than 100 mA. The BPH usually has one embedded function, and power is always available to the controller of the hub. If the embedded function and hub require more than 100 mA on power up, keep the power to the embedded function off until enumeration is completed. This can be accomplished by removing power or by shutting off the clock to the embedded function. Power-switching the embedded function is not necessary if the aggregate power draw for the function and controller is less than 100 mA. The total current drawn by the buspowered device is the sum of the current to the controller, the embedded function, and the downstream ports, and it is limited to 500 mA from an upstream port.

11.2 Low-Power Bus-Powered and High-Power Bus-Powered Functions

Both low-power and high-power bus-powered functions obtain all power from upstream ports. Low-power functions always draw less than 100 mA; high-power functions must draw less than 100 mA at power up and can draw up to 500 mA after enumeration. If the load of the function is more than the parallel combination of 44 Ω and 10 μ F at power up, the device must implement inrush current limiting.

11.3 Power Dissipation and Junction Temperature

The low ON-resistance of the N-channel MOSFET allows small surface-mount packages to pass large currents. It is good design practice to estimate power dissipation and junction temperature. The below analysis gives an approximation for calculating junction temperature based on the power dissipation in the package. However, it is important to note that thermal analysis is strongly dependent on additional system level factors. Such factors include air flow, board layout, copper thickness and surface area, and proximity to other devices dissipating power. Good thermal design practice must include all system level factors in addition to individual component analysis.

Begin by determining the $r_{DS(on)}$ of the N-channel MOSFET relative to the input voltage and operating temperature. As an initial estimate, use the highest operating ambient temperature of interest and read $r_{DS(on)}$ from the typical characteristics graph. Using this value, the power dissipation can be calculated using Equation 7.

 $P_D = r_{DS(on)} \times I_{OUT}^2$

where

- P_D = Total power dissipation (W)
- $r_{DS(on)}$ = Power switch on-resistance (Ω)
- I_{OUT} = Maximum current-limit threshold (A)
- This step calculates the total power dissipation of the N-channel MOSFET.

Finally, calculate the junction temperature:

 $T_{J} = P_{D} \times \theta_{JA} + T_{A}$

where

- T_A = Ambient temperature (°C)
- θ_{JA} = Thermal resistance (°C/W)
- P_D = Total power dissipation (W)

(8)

(7)

Compare the calculated junction temperature with the initial estimate. If they are not within a few degrees, repeat the calculation using the *refined* $r_{DS(on)}$ from the previous calculation as the new estimate. Two or three iterations are generally sufficient to achieve the desired result. The final junction temperature is highly dependent on thermal resistance θ_{JA} , and thermal resistance is highly dependent on the individual package and board layout. The *Thermal Information* table provides example thermal resistances for specific packages and board layouts.

24 Submit Documentation Feedback



25

12 Layout

12.1 Layout Guidelines

- TI recommends placing the 100-nF bypass capacitor near the IN and GND pins, and make the connections using a low-inductance trace.
- TI recommends placing a high-value electrolytic capacitor and a 100-nF bypass capacitor on the output pin when large transient currents are expected on the output.
- The traces routing the RILIM resistor to the device must be as short as possible to reduce parasitic effects on the current limit accuracy.
- The PowerPAD must be directly connected to PCB ground plane using wide and short copper trace.

12.2 Layout Example

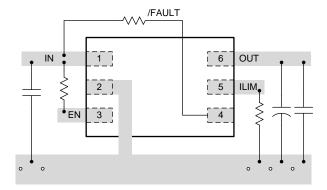


Figure 30. Layout Recommendation

13 Device and Documentation Support

13.1 Device Support

For the TI Switch Portfolio, go here.

13.2 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

PARTS	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
TPS32552	Click here	Click here	Click here	Click here	Click here
TPS2553	Click here	Click here	Click here	Click here	Click here
TPS2552-1	Click here	Click here	Click here	Click here	Click here
TPS2553-1	Click here	Click here	Click here	Click here	Click here

Table 5. Related Links

13.3 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

13.4 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E[™] Online Community *TI's Engineer-to-Engineer (E2E) Community.* Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support TI's Design Support Quickly find helpful E2E forums along with design support tools and contact information for technical support.

13.5 Trademarks

PowerPAD, E2E are trademarks of Texas Instruments. All other trademarks are the property of their respective owners.

13.6 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

13.7 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

14 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



15-Apr-2017

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
HPA00615DRVR	(1) ACTIVE	WSON	DRV	6	3000	(2) Green (RoHS & no Sb/Br)	(6) CU NIPDAU	(3) Level-1-260C-UNLIM	-40 to 85	(4/5) CHT	Samples
HPA00714DBVR	ACTIVE	SOT-23	DBV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	2552	Samples
HPA02257DBVR	ACTIVE	SOT-23	DBV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	CHZ	Samples
TPS2552DBVR	ACTIVE	SOT-23	DBV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	2552	Samples
TPS2552DBVR-1	ACTIVE	SOT-23	DBV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	СНХ	Samples
TPS2552DBVT	ACTIVE	SOT-23	DBV	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	2552	Samples
TPS2552DBVT-1	ACTIVE	SOT-23	DBV	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	СНХ	Samples
TPS2552DRVR	ACTIVE	WSON	DRV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	CHR	Samples
TPS2552DRVR-1	ACTIVE	WSON	DRV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	СНҮ	Samples
TPS2552DRVT	ACTIVE	WSON	DRV	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	CHR	Samples
TPS2552DRVT-1	ACTIVE	WSON	DRV	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	СНҮ	Samples
TPS2553DBVR	ACTIVE	SOT-23	DBV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	2553	Samples
TPS2553DBVR-1	ACTIVE	SOT-23	DBV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	CHZ	Samples
TPS2553DBVT	ACTIVE	SOT-23	DBV	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	2553	Samples
TPS2553DBVT-1	ACTIVE	SOT-23	DBV	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	CHZ	Samples
TPS2553DRVR	ACTIVE	WSON	DRV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	СНТ	Samples
TPS2553DRVR-1	ACTIVE	WSON	DRV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	CJZ	Samples



15-Apr-2017

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TPS2553DRVT	ACTIVE	WSON	DRV	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	СНТ	Samples
TPS2553DRVT-1	ACTIVE	WSON	DRV	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	CJZ	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

15-Apr-2017

OTHER QUALIFIED VERSIONS OF TPS2553, TPS2553-1 :

• Automotive: TPS2553-Q1, TPS2553-Q1

NOTE: Qualified Version Definitions:

• Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

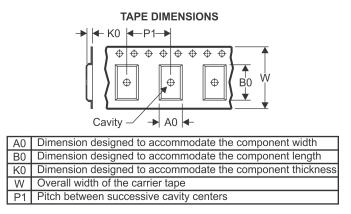
PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS2552DBVR	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS2552DBVR	SOT-23	DBV	6	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
TPS2552DBVR-1	SOT-23	DBV	6	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
TPS2552DBVR-1	SOT-23	DBV	6	3000	179.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS2552DBVT	SOT-23	DBV	6	250	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS2552DBVT	SOT-23	DBV	6	250	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
TPS2552DBVT	SOT-23	DBV	6	250	179.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS2552DBVT-1	SOT-23	DBV	6	250	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
TPS2552DBVT-1	SOT-23	DBV	6	250	179.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS2552DRVR	WSON	DRV	6	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TPS2552DRVR-1	WSON	DRV	6	3000	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS2552DRVT	WSON	DRV	6	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TPS2552DRVT-1	WSON	DRV	6	250	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS2553DBVR	SOT-23	DBV	6	3000	179.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS2553DBVR	SOT-23	DBV	6	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
TPS2553DBVR-1	SOT-23	DBV	6	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
TPS2553DBVR-1	SOT-23	DBV	6	3000	179.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS2553DBVR-1	SOT-23	DBV	6	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3

PACKAGE MATERIALS INFORMATION

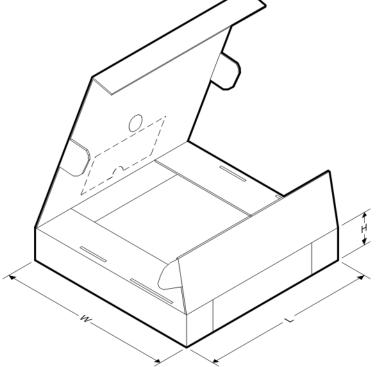


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20-Jan-2018

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS2553DBVT	SOT-23	DBV	6	250	179.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS2553DBVT	SOT-23	DBV	6	250	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
TPS2553DBVT-1	SOT-23	DBV	6	250	179.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS2553DBVT-1	SOT-23	DBV	6	250	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
TPS2553DRVR	WSON	DRV	6	3000	179.0	8.4	2.2	2.2	1.2	4.0	8.0	Q2
TPS2553DRVR	WSON	DRV	6	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TPS2553DRVR-1	WSON	DRV	6	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TPS2553DRVT	WSON	DRV	6	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
TPS2553DRVT-1	WSON	DRV	6	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2





*All dimensions are nominal							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS2552DBVR	SOT-23	DBV	6	3000	210.0	185.0	35.0
TPS2552DBVR	SOT-23	DBV	6	3000	180.0	180.0	18.0
TPS2552DBVR-1	SOT-23	DBV	6	3000	180.0	180.0	18.0
TPS2552DBVR-1	SOT-23	DBV	6	3000	203.0	203.0	35.0
TPS2552DBVT	SOT-23	DBV	6	250	210.0	185.0	35.0
TPS2552DBVT	SOT-23	DBV	6	250	180.0	180.0	18.0
TPS2552DBVT	SOT-23	DBV	6	250	203.0	203.0	35.0
TPS2552DBVT-1	SOT-23	DBV	6	250	180.0	180.0	18.0

PACKAGE MATERIALS INFORMATION



www.ti.com

20-Jan-2018

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS2552DBVT-1	SOT-23	DBV	6	250	203.0	203.0	35.0
TPS2552DRVR	WSON	DRV	6	3000	210.0	185.0	35.0
TPS2552DRVR-1	WSON	DRV	6	3000	203.0	203.0	35.0
TPS2552DRVT	WSON	DRV	6	250	210.0	185.0	35.0
TPS2552DRVT-1	WSON	DRV	6	250	203.0	203.0	35.0
TPS2553DBVR	SOT-23	DBV	6	3000	203.0	203.0	35.0
TPS2553DBVR	SOT-23	DBV	6	3000	180.0	180.0	18.0
TPS2553DBVR-1	SOT-23	DBV	6	3000	180.0	180.0	18.0
TPS2553DBVR-1	SOT-23	DBV	6	3000	203.0	203.0	35.0
TPS2553DBVR-1	SOT-23	DBV	6	3000	210.0	185.0	35.0
TPS2553DBVT	SOT-23	DBV	6	250	203.0	203.0	35.0
TPS2553DBVT	SOT-23	DBV	6	250	180.0	180.0	18.0
TPS2553DBVT-1	SOT-23	DBV	6	250	203.0	203.0	35.0
TPS2553DBVT-1	SOT-23	DBV	6	250	180.0	180.0	18.0
TPS2553DRVR	WSON	DRV	6	3000	203.0	203.0	35.0
TPS2553DRVR	WSON	DRV	6	3000	210.0	185.0	35.0
TPS2553DRVR-1	WSON	DRV	6	3000	210.0	185.0	35.0
TPS2553DRVT	WSON	DRV	6	250	210.0	185.0	35.0
TPS2553DRVT-1	WSON	DRV	6	250	210.0	185.0	35.0

DRV 6

GENERIC PACKAGE VIEW

WSON - 0.8 mm max height PLASTIC SMALL OUTLINE - NO LEAD



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



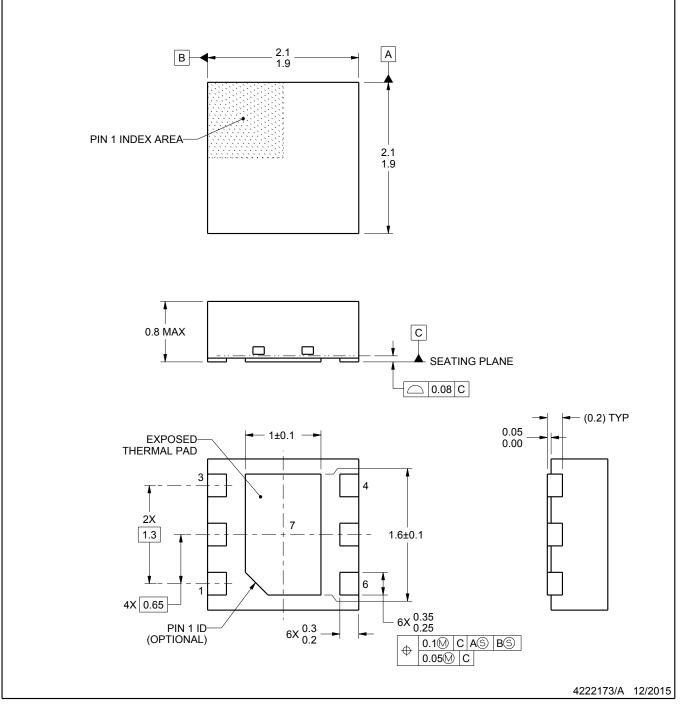
DRV0006A



PACKAGE OUTLINE

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.2. This drawing is subject to change without notice.3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

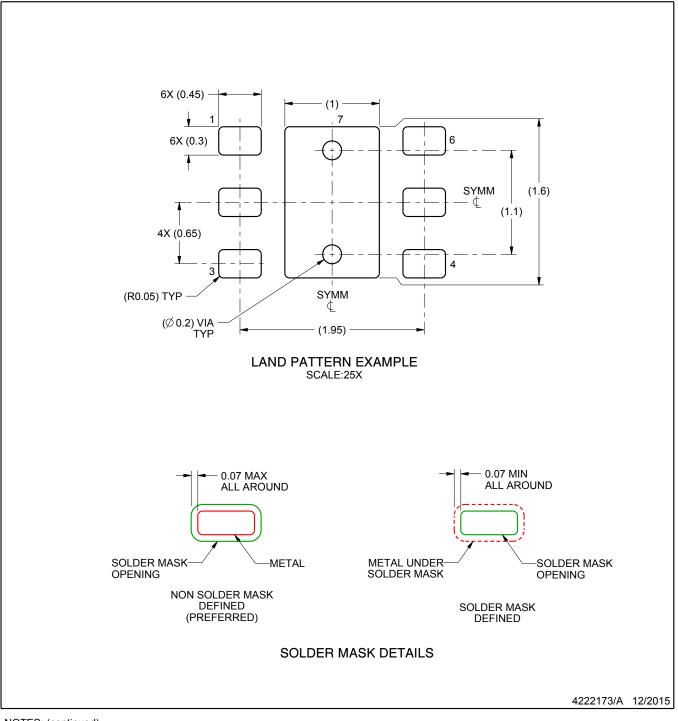


DRV0006A

EXAMPLE BOARD LAYOUT

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature

number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.

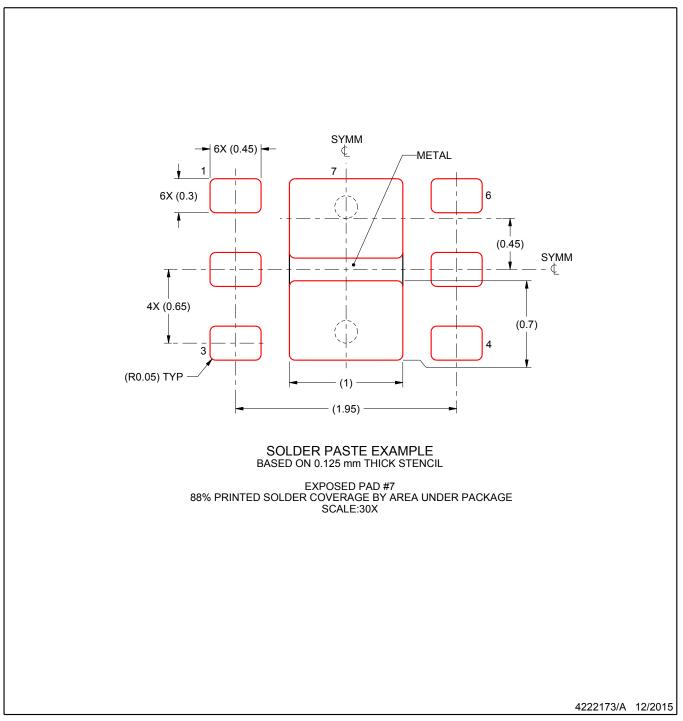


DRV0006A

EXAMPLE STENCIL DESIGN

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



DBV (R-PDSO-G6)

PLASTIC SMALL-OUTLINE PACKAGE



- NOTES:
 - A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
 - D. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
 - È Falls within JEDEC MO-178 Variation AB, except minimum lead width.



LAND PATTERN DATA



NOTES:

- A. All linear dimensions are in millimeters.B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.



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